

10A LOW VF SCHOTTKY BARRIER RECTIFIER

Features

- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Maximum Junction Temperature Rating
- Very Low Forward Voltage Drop
- Very Low Leakage Current
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- Plastic Material: UL Flammability Classification Rating 94V-0

Mechanical Data

Case: DPAK Molded Plastic

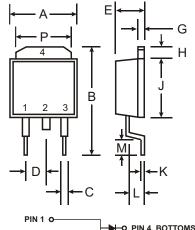
Terminals: Solderable per MIL-STD-202,

Method 208

Polarity: See Diagram

Marking Information: See Page 2

Weight: 0.4 grams (approx.)



PIN 1 O PIN 4, BOTTOMSIDE HEAT SINK

DPAK Min Dim Max Α 6.3 6.7 В 10 С 0.3 8.0 D 2.3 Nominal Ε 2.1 2.5 G 0.4 0.6 н 1.2 1.6 J 5.3 5.7 Κ 0.5 Nominal L 1.3 1.8 M 1.0 Р 5.1 5.5 All Dimensions in mm

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Note: Pins 1 & 3 must be electrically connected at the printed circuit board.

Maximum Ratings @ T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

| Characteristic | Symbol | Value | Unit |
|---|--|-------------|------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V _{RRM} V _{RWM} V _R | 40 | V |
| RMS Reverse Voltage | V _{R(RMS)} | 28 | V |
| Average Rectified Output Current (Also see Figure 4) | Io | 10 | Α |
| Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave Superimposed on Rated Load (JEDEC Method) | I _{FSM} | 100 | А |
| Typical Thermal Resistance Junction to Case | R ₀ JC | 6.0 | °C/W |
| Typical Thermal Resistance Junction to Ambient | R ₀ JA | 80 | °C/W |
| Operating Temperature Range | Tj | -65 to +150 | °C |
| Storage Temperature Range | T _{STG} | -65 to +150 | °C |

Electrical Characteristics @ T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|------------------------------------|--------------------|-----|-------------------|----------------------|------|--|
| Reverse Breakdown Voltage (Note 1) | V _{(BR)R} | 40 | _ | _ | V | I _R = 1mA |
| Forward Voltage (Note 1) | V _{FM} | _ | 0.45 — 0.47 | 0.49 0.41 0.51 | V | I _F = 8A, T _S = 25°C I _F = 8A, T _S = 125°C I _F = 10A, T _S = 25°C |
| Peak Reverse Current (Note 1) | I _{RM} | _ | 0.1 12.5 | 0.3 25 | mA | T _S = 25°C, V _R = 35V T _S = 100°C, V _R = 35V |
| Junction Capacitance | Cj | _ | 700 | _ | pF | f = 1.0MHz, V _R = 4.0V DC |

Notes: 1. Short duration test pulse used to minimize self-heating effect.



Ordering Information (Note 2)

| Device | Packaging | Shipping |
|------------|-----------|------------------|
| MBRD1040-T | DPAK | 2500/Tape & Reel |

Notes: 2. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

10,000

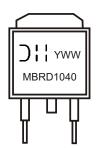
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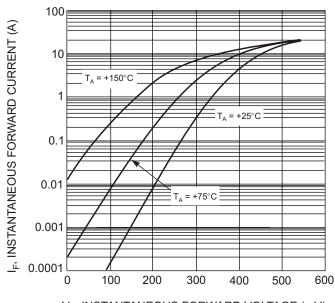
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Cj, JUNCTION CAPACITANCE (pF)



MBRD1040 = Product type marking code
DH = Manufacturers' code marking
YWW = Date code marking
Y = Last digit of year ex: 2 for 2002
WW = Week code 01 to 52



V_F, INSTANTANEOUS FORWARD VOLTAGE (mV) Fig. 1 Typical Forward Characteristics



 $\label{eq:VR} {\rm V_R,\,REVERSE\,\,VOLTAGE\,\,(V)}$ Fig. 3 Typical Junction Capacitance vs. Reverse Voltage

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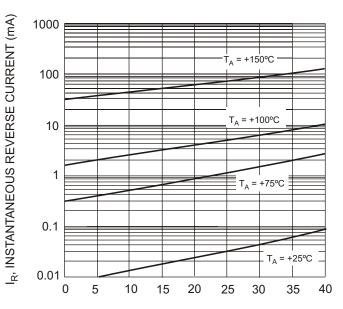
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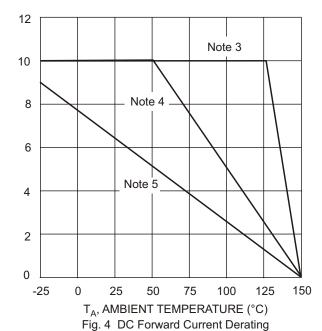
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V_R, INSTANTANEOUS REVERSE VOLTAGE (V) Fig. 2 Typical Reverse Characteristics





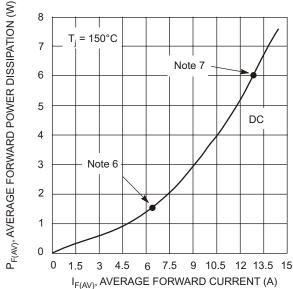


Fig. 5 Forward Power Dissipation (Per Element)

Notes:

- 3. $T_A = T_{SOLDERING\ POINT}$, $R_{\theta JC} = 6.0^{\circ} C/W$, $R_{\theta CA} = 0^{\circ} C/W$.
- 4. Device mounted on GETEK substrate, 2"x2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". $R_{\theta JA}$ in range of 15-30°C/W.
- Device mounted on FR-4 substrate, 2"x2", 2 oz. copper, single-sided, pad layout as per Diodes Inc. suggested pad layout document AP02001 which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. R_{θJA} in range of 60-75°C/W.
- 6. Maximum power disspiation when the device is mounted in accordance to the conditions described in Note 5.
- 7. Maximum power dissipation when the device is mounted in accordance to the conditions described in Note 4.